

ABSTRACT

A patterning method is provided. First, a substrate comprising a film formed thereon is provided. Then, a photoresist layer is formed over the film. Next, the photoresist layer is developed to form a patterned photoresist layer. Then, the film is etched using a dry etching method. In addition, the dry etching method is performed at a temperature range of about -50°C to about 50°C using the patterned photoresist layer as an etching mask.